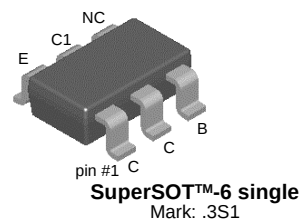


FMBS5551

FMBS5551

NPN General Purpose Amplifier

- This device is designed for general purpose high voltage amplifiers and gas discharge display drivers.



Absolute Maximum Ratings* $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	160	V
V_{CBO}	Collector-Base Voltage	180	V
V_{EBO}	Emitter-Base Voltage	6.0	V
I_C	Collector Current - Continuous	600	mA
T_J, T_{STG}	Operating and Storage Junction Temperature Range	- 55 ~ 150	$^\circ\text{C}$

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- These ratings are based on a maximum junction temperature of 150 degrees C.
- These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Characteristics					
$V_{(BR)CEO}$	Collector-Emitter Sustaining Voltage *	$I_C = 1.0\text{mA}, I_B = 0$	160		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100\mu\text{A}, I_E = 0$	180		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10\mu\text{A}, I_C = 0$	6.0		V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 120\text{V}, I_E = 0$ $V_{CB} = 120\text{V}, I_E = 0, T_a = 100^\circ\text{C}$		50 50	nA μA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = 4.0\text{V}, I_C = 0$		50	nA
On Characteristics					
h_{FE}	DC Current Gain	$I_C = 1.0\text{mA}, V_{CE} = 5.0\text{V}$ $I_C = 10\text{mA}, V_{CE} = 5.0\text{V}$ $I_C = 50\text{mA}, V_{CE} = 5.0\text{V}$	80 80 30	250	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$		0.15 0.2	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$		1.0 1.0	V
Small Signal Characteristics					
f_T	Current Gain Bandwidth Product	$I_C = 10\text{mA}, V_{CE} = 10, f = 100\text{MHz}$	100	300	MHz
C_{obo}	Output Capacitance	$V_{CE} = 10\text{V}, I_C = 0, f = 1.0\text{MHz}$		6.0	pF
C_{ibo}	Input Capacitance	$V_{BE} = 0.5\text{V}, I_C = 0, f = 1.0\text{MHz}$		20	pF
h_{fe}	Small Single Current Gain	$I_C = 1.0\text{mA}, V_{CE} = 10\text{V}, f = 1.0\text{KHz}$	50	250	
N_F	Noise Figure	$I_C = 250\mu\text{A}, V_{CE} = 5.0\text{V},$ $R_S = 1.0\text{K}\Omega, f = 10\text{Hz to } 15.7\text{KHz}$		8.0	dB

* Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2.0\%$

Thermal Characteristics $T_a=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Max.	Units
P_D	Total Device Dissipation *	700	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, total	180	$^{\circ}\text{C/W}$

* Device mounted on a 1 in 2 pad of 2 oz copper.

Typical Characteristics

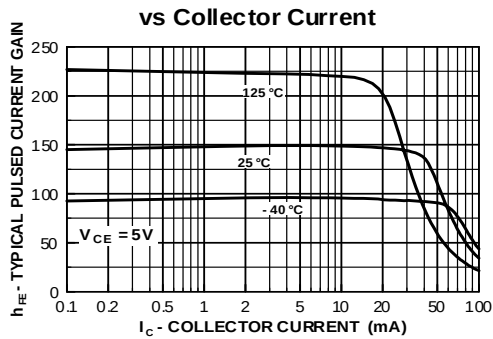


Figure 1. Typical Pulsed Current Gain vs Collector Current

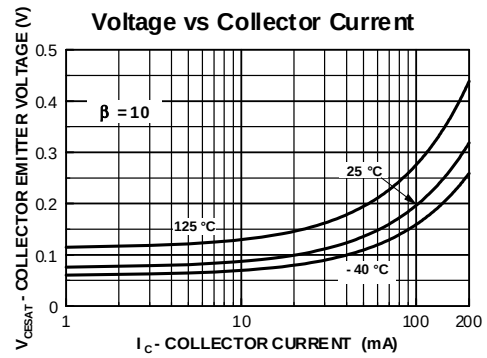


Figure 2. Collector-Emitter Saturation Voltage vs Collector Current

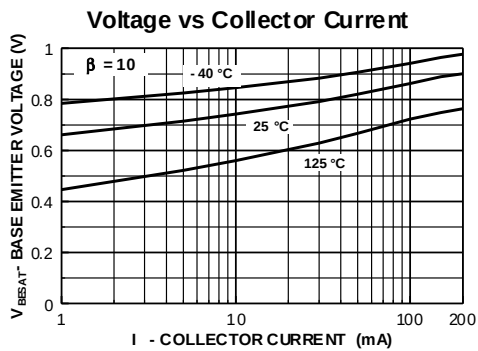


Figure 3. Base-Emitter Saturation Voltage vs Collector Current

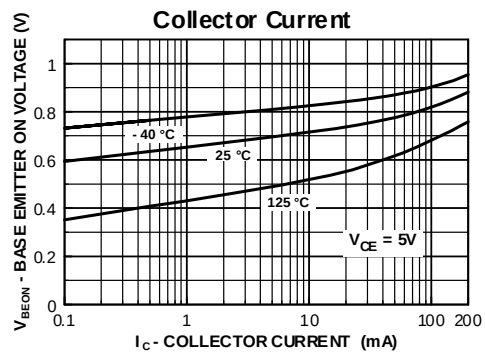


Figure 4. Base-Emitter On Voltage vs Collector Current

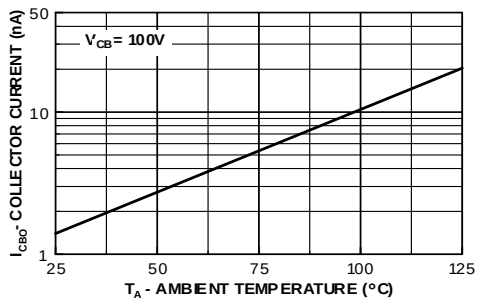


Figure 5. Collector Cutoff Current vs Ambient Temperature

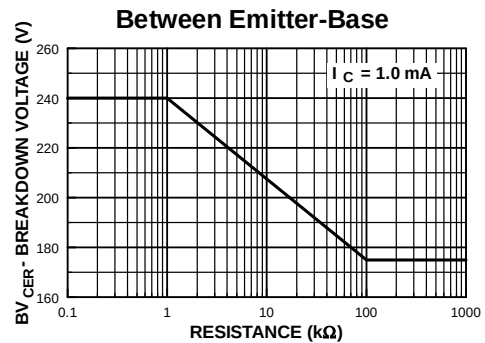


Figure 6. Collector-Emitter Breakdown Voltage with Resistance Between Emitter-Base

Typical Characteristics (Continued)

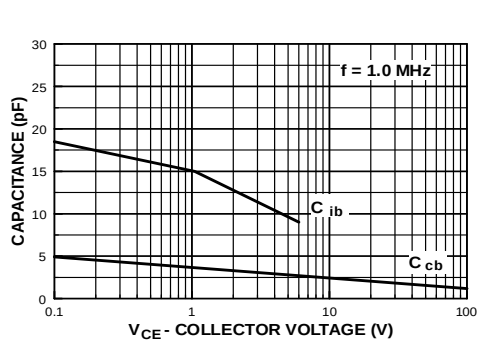


Figure 7. Input and Output Capacitance vs Reverse Voltage

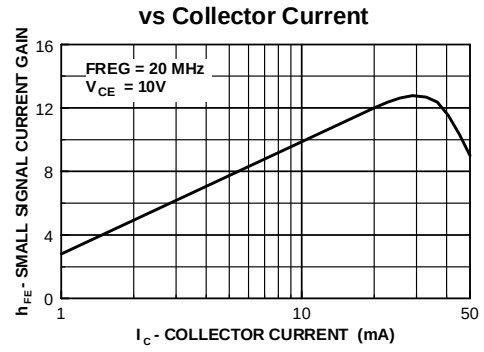
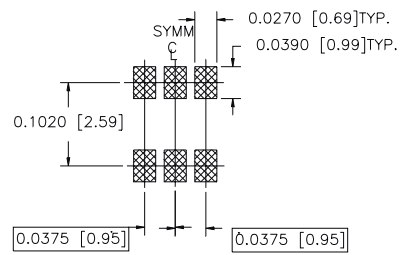
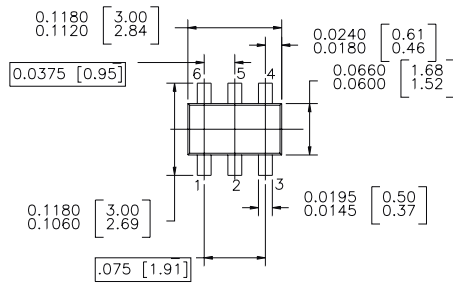


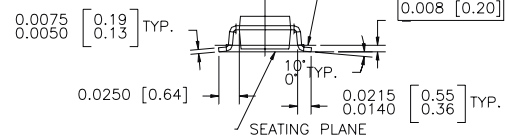
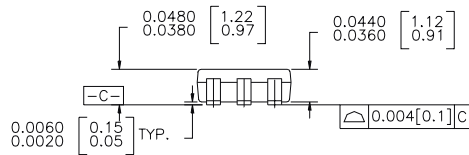
Figure 8. Small Signal current Gain vs Collector Current

Package Dimensions

SuperSOT™-6



LAND PATTERN RECOMMENDATION



NOTES : UNLESS OTHERWISE SPECIFIED

1.0 STANDARD LEAD FINISH : 150 MICROINCHES 93.81 MICROMETERS)
MINIMUM TIN / LEAD (SOLDER) ON COPPER.

2.0 NO JEDEC REGISTRATION AS OF JULY 1996

SUPER SOT 6 LEADS

Dimensions in Millimeters

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CROSSVOLT™	GlobalOptoisolator™	MicroPak™	QFET [®]	SuperSOT™-8
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EcoSPARK™	HiSeC™	MSX™	QT Optoelectronics™	TinyLogic [®]
E ² CMOS™	I ² C™	MSXPro™	Quiet Series™	TINYOPTO™
EnSigna™	i-Lo™	OCX™	RapidConfigure™	TruTranslation™
FACT™	ImpliedDisconnect™	OCXPro™	RapidConnect™	UHC™
FACT Quiet Series™		OPTOLOGIC [®]	μSerDes™	UltraFET [®]
Across the board. Around the world.™		OPTOPLANAR™	SILENT SWITCHER [®]	VCX™
The Power Franchise [®]		PACMAN™	SMART START™	
Programmable Active Droop™		POP™	SPM™	

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